

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**PATENT** 

In re application of: O'DONNELL

Application No.: 09/472,757

Filed: December 27, 1999

Title: INSITU POST ETCH PROCESS TO REMOVE REMAINING PHOTORESIST AND RESIDUAL SIDEWALL PASSIVATION

Attorney Docket Inc.
LAM1P133/P0582

Examiner: UMEZ ERONINI/Proette 1.

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**CERTIFICATE OF MAILING** 

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail to: Box AF, Commissioner for Patents, Washington, D.C. 20231 on February 27, 2003.

AMENDMENT D

Box AF Commissioner for Patents Washington, D.C. 20231

E/A L.J.M-E 4/23/2003

Dear Madame:

This is in response to the Final Office Action mailed January 2, 2003. Please consider the following remarks and amend the above-identified patent application as follows:

## In the Claims:

Please cancel claim 20 and amend claims 1, 15, 17, and 19, as follows:

1. (Once Amended) A method for etching at least partially through a metal-containing layer disposed above a substrate, wherein part of said metal-containing layer is disposed below an etch mask and part of said metal-containing layer is not disposed below the etch mask, comprising the steps of:

placing the substrate in an etch chamber;

flowing an etchant gas into the etch chamber;